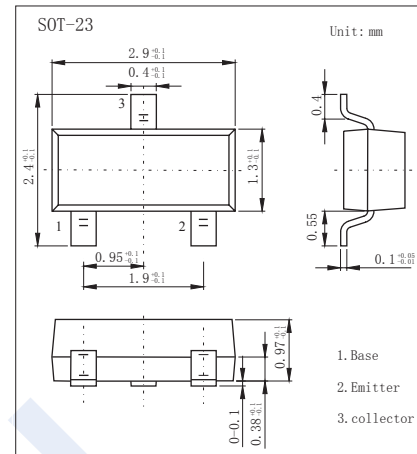


PNP Transistors

2SB792

■ Features

- High collector to emitter voltage V_{CE0} .
- Low noise voltage NV
- Complimentary to 2SD814.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-150	V
Collector - Emitter Voltage	V_{CE0}	-150	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-50	mA
Collector Current - Pulse	I_{CP}	-100	
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}$, $I_E = 0$	-150			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 \text{ mA}$, $I_B = 0$	-150			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}$, $I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -100 \text{ V}$, $I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4 \text{ V}$, $I_C = 0$			-1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -30 \text{ mA}$, $I_B = -3 \text{ mA}$			-1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -30 \text{ mA}$, $I_B = -3 \text{ mA}$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -5 \text{ V}$, $I_C = -10 \text{ mA}$	130		450	
Noise voltage	NV	$V_{CE} = -10 \text{ V}$, $I_C = -1 \text{ mA}$, $G_v = 80 \text{ dB}$, $R_g = 100 \text{ k}\Omega$, Function = FLAT		150		mV
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		4		pF
Transition frequency	f_T	$V_{CE} = -10 \text{ V}$, $I_E = 10 \text{ mA}$, $f = 200 \text{ MHz}$		200		MHz

■ Classification of h_{FE}

Type	2SB792-R	2SB792-S	2SB792-T
Range	130-220	185-330	260-450
Marking	IR	IS	IT

PNP Transistors

2SB792

Typical Characteristics

